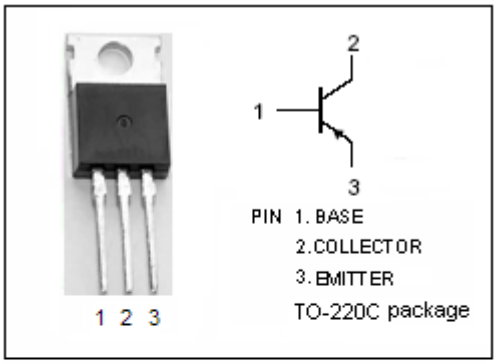
isc Silicon PNP Power Transistor 2SB689



DESCRIPTION

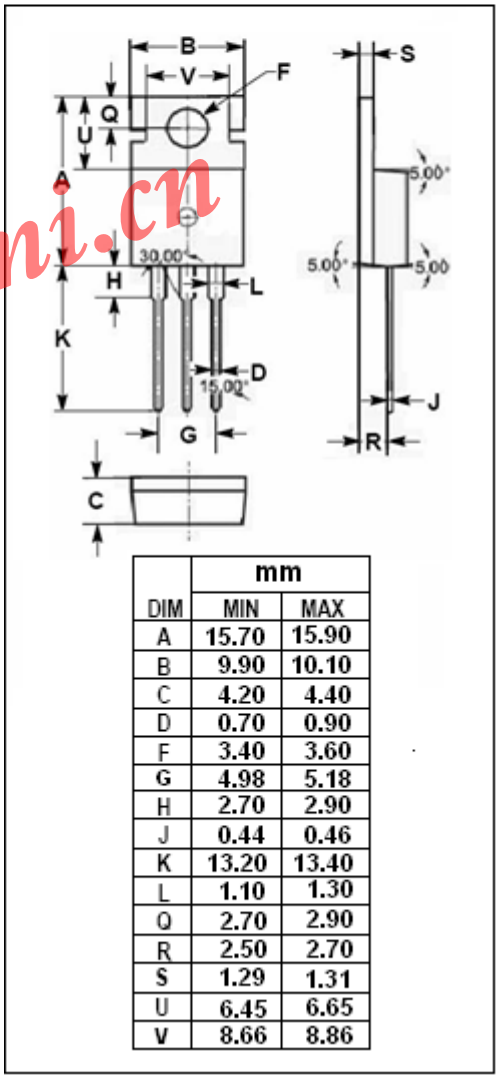
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$ = -100V(Min)
- High Power Dissipation
- Wide Area of Safe Operation

APPLICATIONS

- Designed for low frequency power amplifier and TV vertical deflection output applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-4	V
I_C	Collector Current-Continuous	-4	A
I_{CM}	Collector Current-Peak	-5	A
P_C	Total Power Dissipation @ T_a=25℃	1.8	W
	Total Power Dissipation @ T_C=25℃	40	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-45~150	℃



DIM	mm MIN	MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA; R_{BE}= ∞	-100			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -1mA; I_C= 0	-4			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -1A; I_B= -0.1A			-1.0	V
I_{CEO}	Collector Cutoff Current	V_{CE}= -80V; R_{BE}= ∞			-100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -3.5V; I_C= 0			-50	μA
h_{FE-1}	DC Current Gain	I_C= -0.5A; V_{CE}= -4V	50		250	
h_{FE-2}	DC Current Gain	I_C= -50mA; V_{CE}= -4V	25		350	